

# N-Channel 100-V (D-S) 175 °C MOSFET

## PRODUCT SUMMARY

$V_{DS}$ (V)	$r_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
100	0.024 at $V_{GS} = 10$ V	47
	0.027 at $V_{GS} = 4.5$ V	44

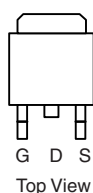
## FEATURES

- TrenchFET® Power MOSFET
- 175 °C Maximum Junction Temperature
- 100 %  $R_g$  Tested

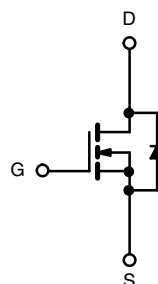


**RoHS**  
COMPLIANT

TO-263



Ordering Information: SUM47N10-24L-E3 (Lead (Pb)-free)



N-Channel MOSFET

## ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current ( $T_J = 175$ °C) <sup>b</sup>	$I_D$	47	A
		27	
Pulsed Drain Current	$I_{DM}$	70	
Continuous Source Current (Diode Conduction)	$I_S$	47	
Single Pulse Avalanche Current	$I_{AS}$	40	mJ
Single Pulse Avalanche Energy (Duty Cycle $\leq 1$ %)	$E_{AS}$	80	
Maximum Power Dissipation	$P_D$	136 <sup>b</sup>	W
		3.75 <sup>a</sup>	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 175	°C

## THERMAL RESISTANCE RATINGS

Parameter	Symbol	Maximum	Unit
Junction-to-Ambient	$R_{thJA}$	40	°C/W
		62.5	
Junction-to-Case	$R_{thJC}$	1.1	

Notes:

a. Surface Mounted on 1" x 1" FR4 Board.

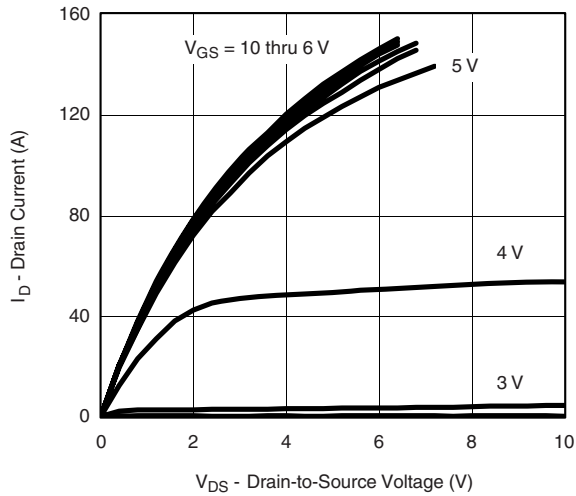
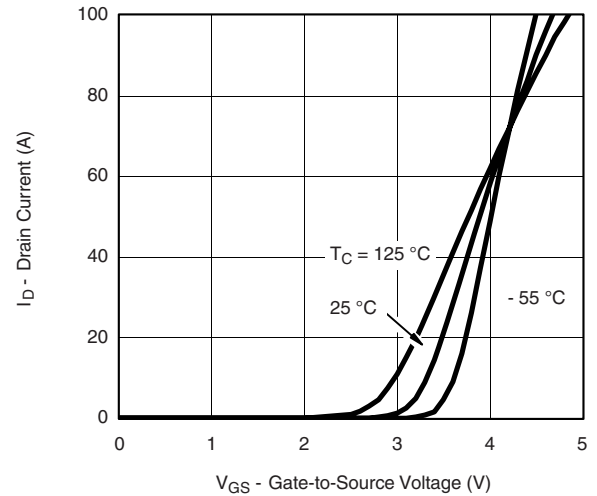
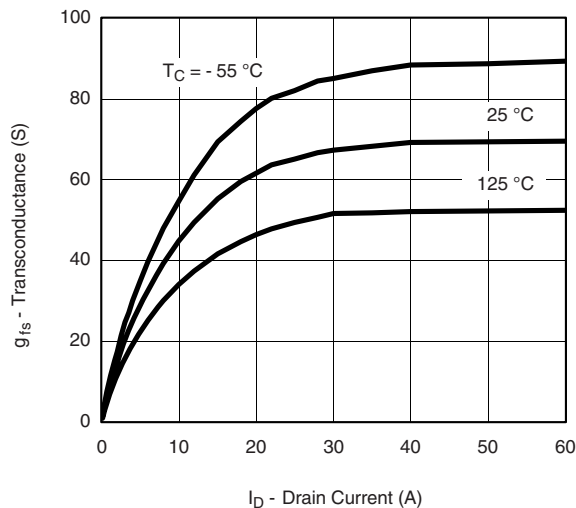
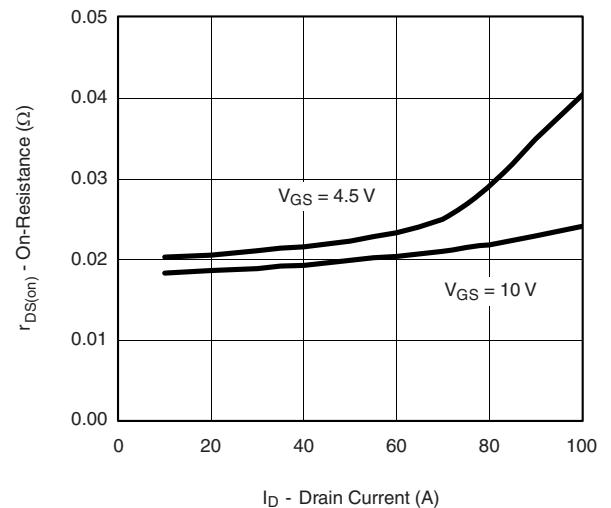
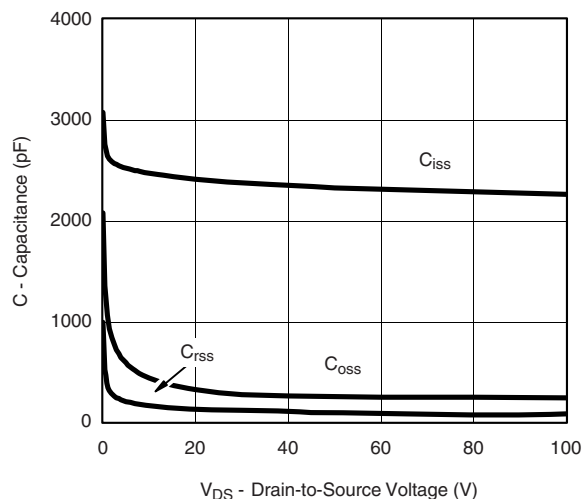
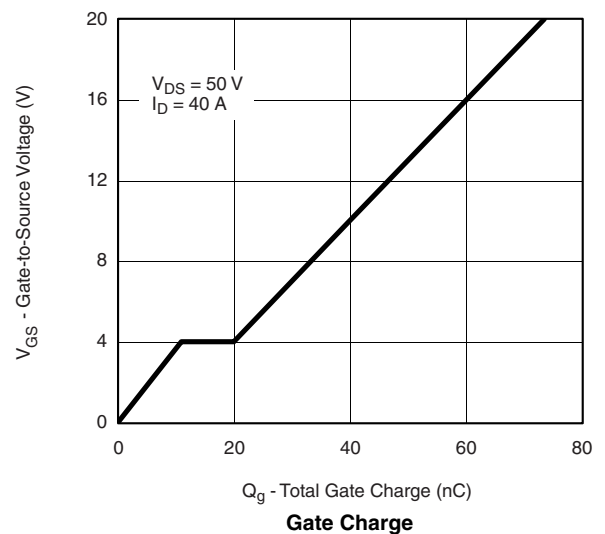
b. See SOA curve for voltage derating.

SPECIFICATIONS T <sub>J</sub> = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	100			V
Gate-Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.0		3.0	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V			1	μA
		V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			50	
		V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C			250	
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	70			A
Drain-Source On-State Resistance <sup>b</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 40 A		0.019	0.024	Ω
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 40 A, T <sub>J</sub> = 125 °C			0.048	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 40 A, T <sub>J</sub> = 175 °C			0.060	
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 20 A		0.021	0.027	
Forward Transconductance <sup>b</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 40 A		70		S
Dynamic <sup>a</sup>						
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, F = 1 MHz		2400		pF
Output Capacitance	C <sub>oss</sub>			290		
Reverse Transfer Capacitance	C <sub>rss</sub>			120		
Total Gate Charge <sup>c</sup>	Q <sub>g</sub>	V <sub>DS</sub> = 50 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 40 A		40	60	nC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>			11		
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			9		
Gate Resistance	R <sub>g</sub>	f = 1 MHz	1	2.2	3.5	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	V <sub>DD</sub> = 50 V, R <sub>L</sub> = 1.25 Ω I <sub>D</sub> ≅ 47 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 2.5 Ω		8	13	ns
Rise Time <sup>c</sup>	t <sub>r</sub>			40	60	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			15	25	
Fall Time <sup>c</sup>	t <sub>f</sub>			80	120	
Source-Drain Diode Ratings and Characteristics T <sub>C</sub> = 25 °C						
Pulsed Current	I <sub>SM</sub>				70	A
Diode Forward Voltage <sup>b</sup>	V <sub>SD</sub>	I <sub>F</sub> = 40 A, V <sub>GS</sub> = 0 V		1.0	1.5	V
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 47 A, di/dt = 100 A/μs		75	120	ns

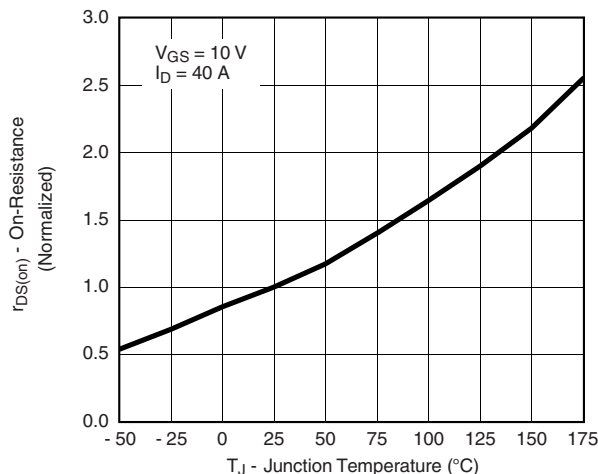
## Notes:

- a. Guaranteed by design, not subject to production testing.  
b. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
c. Independent of operating temperature.

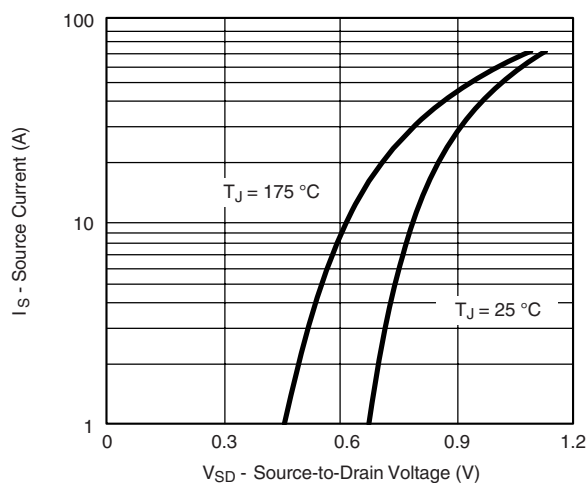
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted**Output Characteristics****Transfer Characteristics****Transconductance****On-Resistance vs. Drain Current****Capacitance****Gate Charge**

## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

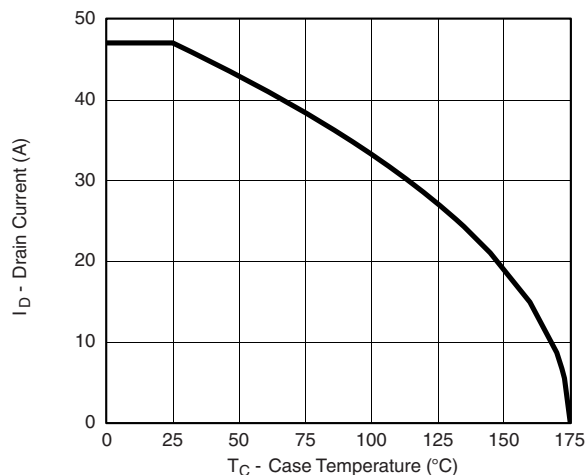


On-Resistance vs. Junction Temperature

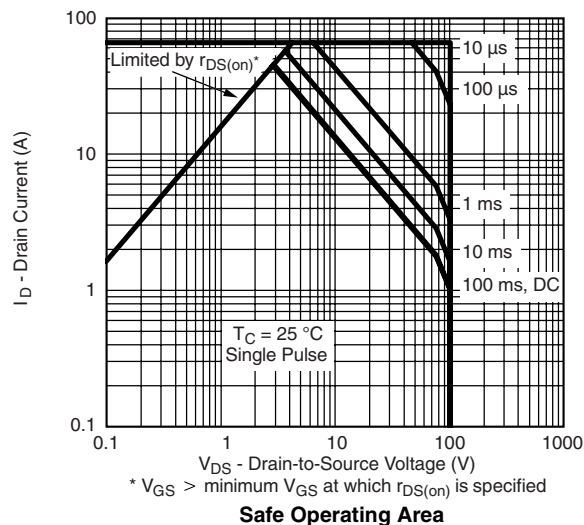


Source-Drain Diode Forward Voltage

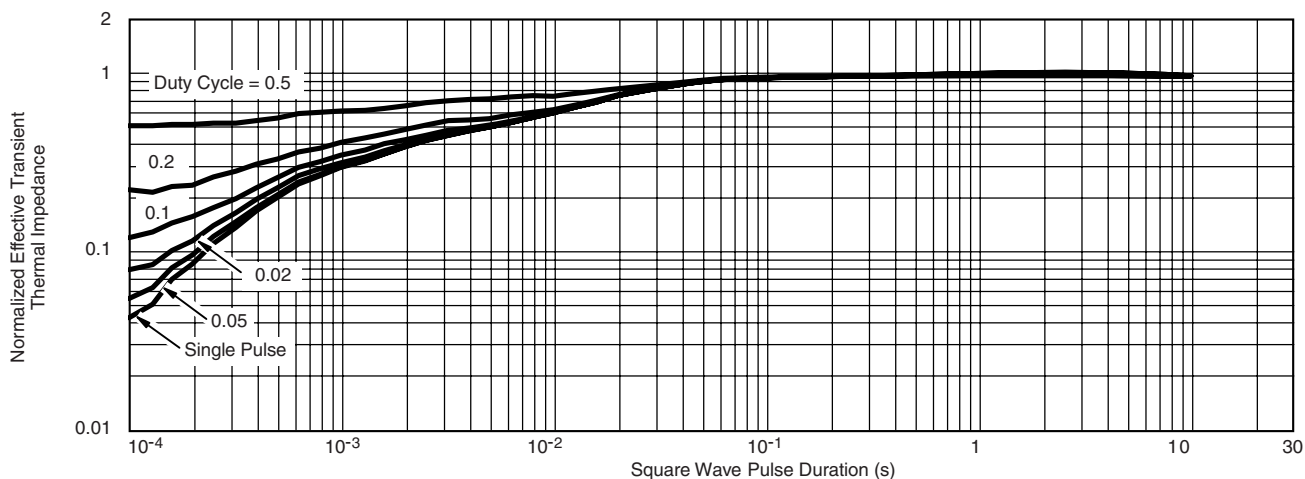
## THERMAL RATINGS



Maximum Avalanche Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

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